

This listing of claims will replace all prior versions of claims in the application.

Claims 1-87. (cancelled)

Claim 88. (new) A method for forming a photoresist relief image, comprising:

- (a) applying over an integrated circuit substrate a coating layer of an organic antireflective composition that comprises i) a silsesquioxane resin and ii) an organic polymer that comprises one or more anthracene groups;
- (b) applying a coating layer of a photoresist composition over the antireflective composition layer; and
- (c) exposing to patterned radiation and developing the photoresist composition layer to form a photoresist relief image.

Claim 89. (new) The method of claim 88 wherein the photoresist is imaged with radiation having a wavelength of about 248 nm.

Claim 90. (new) The method of claim 88 wherein the antireflective composition further comprises an acid or acid generator compound.

Claim 91. (new) The method of claim 88 wherein the antireflective composition is thermally treated prior to applying the photoresist composition layer.

Claim 92. (new) The method of claim 88 wherein the antireflective composition is crosslinked prior to applying the photoresist composition layer.

Claim 93. (new) The method of claim 88 wherein the antireflective composition is applied over a dielectric layer.

Claim 94. (new) The method of claim 93 wherein the dielectric layer comprises SiO_2 .

Claim 95. (new) The method of claim 93 wherein the dielectric layer comprises an organic resin.